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PNP/PNP matched double transistors

Rev. 03 — 28 August 2009

Product data sheet

1. Product profile

1.1 General description

PNP/PNP matched double transistors in small Surface-Mounted Device (SMD) plastic packages. The transistors in the SOT666 and SOT363 (SC-88) packages are fully isolated internally.

Table 1. Product overview

Type number	Package		PNP/PNP h _{FE1} /h _{FE2}	NPN/NPN	
	NXP	JEITA	0.98 complement	complement	
PMP5501V	SOT666	-	PMP5201V	PMP4501V	
PMP5501G	SOT353	SC-88A	PMP5201G	PMP4501G	
PMP5501Y	SOT363	SC-88	PMP5201Y	PMP4501Y	

1.2 Features

- Current gain matching
- Base-emitter voltage matching
- Common emitter configuration for SOT353 types
- Application-optimized pinout

1.3 Applications

- Current mirror
- Differential amplifier

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
V _{CEO}	collector-emitter voltage	open base	-	-	-45	V
I _C	collector current		-	-	-100	mA
h _{FE}	DC current gain	V _{CE} = -5 V; I _C = -2 mA	200	290	450	



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Table 2. Quick reference data continued						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per device)					
h _{FE1} /h _{FE2}	h _{FE} matching	$V_{CE} = -5 V;$ $I_{C} = -2 mA$	<u>[1]</u> 0.95	1	-	
$V_{BE1} - V_{BE2}$	V _{BE} matching	$V_{CE} = -5 V;$ $I_C = -2 mA$	[2] _	-	2	mV

[1] The smaller of the two values is taken as the numerator.

[2] The smaller of the two values is subtracted from the larger value.

Pinning information 2.

Pin	Description	Simplified outline	Symbol		
SOT666;	SOT363				
1	base TR1				
2	base TR2	6 5 4			
3	collector TR2				
4	emitter TR2				
5	emitter TR1		1 2 3 006aaa55		
6	collector TR1	001aab555	00044433		
SOT353					
1	base TR1				
2	emitter TR1, TR2		5 4		
3	base TR2				
4	collector TR2				
5	collector TR1 $\Box_1 \ \Box_2 \ \Box_3$				

Ordering information 3.

Table 4. Orderin	ng informatior	1	
Type number	Package		
	Name	Description	Version
PMP5501V	-	plastic surface-mounted package; 6 leads	SOT666
PMP5501G	SC-88A	plastic surface-mounted package; 5 leads	SOT353
PMP5501Y	SC-88	plastic surface-mounted package; 6 leads	SOT363

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4. Marking

Table 5. Marking codes	
Type number	Marking code ^[1]
PMP5501V	ED
PMP5501G	R4*
PMP5501Y	S6*

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
Per transis	stor				
V _{CBO}	collector-base voltage	open emitter	-	-50	V
V _{CEO}	collector-emitter voltage	open base	-	-45	V
V _{EBO}	emitter-base voltage	open collector	-	-5	V
I _C	collector current		-	-100	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT666		[1][2] _	200	mW
	SOT353		<u>[1]</u> _	200	mW
	SOT363		<u>[1]</u> _	200	mW
Per device	;				
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT666		[1][2] _	300	mW
	SOT353		<u>[1]</u> _	300	mW
	SOT363		<u>[1]</u> _	300	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

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6. Thermal characteristics

Table 7.	Thermal characteristics	5				
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Per trans	istor					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	SOT666		[1][2]	-	625	K/W
	SOT353		<u>[1]</u> _	-	625	K/W
	SOT363		<u>[1]</u> _	-	625	K/W
Per devic	e					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	SOT666		[1][2] _	-	416	K/W
	SOT353		<u>[1]</u> _	-	416	K/W
	SOT363		<u>[1]</u> _	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

7. Characteristics

Table 8.Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
I _{CBO}	collector-base cut-off current	V _{CB} = -30 V; I _E = 0 A	-	-	-15	nA
		V _{CB} = -30 V; I _E = 0 A; T _j = 150 °C	-	-	-5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 V;$ $I_C = 0 A$	-	-	-100	nA
h _{FE}	h _{FE} DC current gain	$V_{CE} = -5 V;$ $I_{C} = -10 \mu A$	-	250	-	
		$V_{CE} = -5 V;$ $I_{C} = -2 mA$	200	290	450	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -10 \text{ mA};$ $I_{B} = -0.5 \text{ mA}$	-	-50	-200	mV
		$I_{C} = -100 \text{ mA};$ $I_{B} = -5 \text{ mA}$	-	-200	-400	mV
V _{BEsat}	base-emitter saturation voltage	$I_{C} = -10 \text{ mA};$ $I_{B} = -0.5 \text{ mA}$	<u>[1]</u> -	-760	-	mV
		l _C = –100 mA; l _B = –5 mA	<u>[1]</u> -	-920	-	mV

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{BE}	base-emitter voltage	V _{CE} = -5 V; I _C = -2 mA	[2] -600	-650	-700	mV
		$V_{CE} = -5 V;$ $I_{C} = -10 mA$	<u>[2]</u> _	-	-760	mV
C _c	collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2.2	pF
C _e	emitter capacitance	$V_{EB} = -0.5 \text{ V};$ $I_C = i_c = 0 \text{ A};$ f = 1 MHz	-	10	-	pF
f _T	transition frequency	$V_{CE} = -5 V;$ $I_{C} = -10 mA;$ f = 100 MHz	100	175	-	MHz
NF	noise figure	$V_{CE} = -5 V;$ $I_{C} = -0.2 mA;$ $R_{S} = 2 k\Omega;$ f = 10 Hz to 15.7 kHz	-	1.6	-	dB
	$V_{CE} = -5 V; \\ I_{C} = -0.2 \text{ mA}; \\ R_{S} = 2 \text{ k}\Omega; \\ f = 1 \text{ kHz}; \\ B = 200 \text{ Hz}$	-	3.1	-	dB	
Per device	l.					
h _{FE1} /h _{FE2}	h _{FE} matching	$V_{CE} = -5 V;$ $I_{C} = -2 mA$	<u>[3]</u> 0.95	1	-	
$V_{BE1} - V_{BE2}$	V _{BE} matching	V _{CE} = -5 V; I _C = -2 mA	<u>[4]</u> _	-	2	mV

Characteristics ... continued Table 8.

 $T_{omb} = 25 \,^{\circ}C$ unless otherwise specified

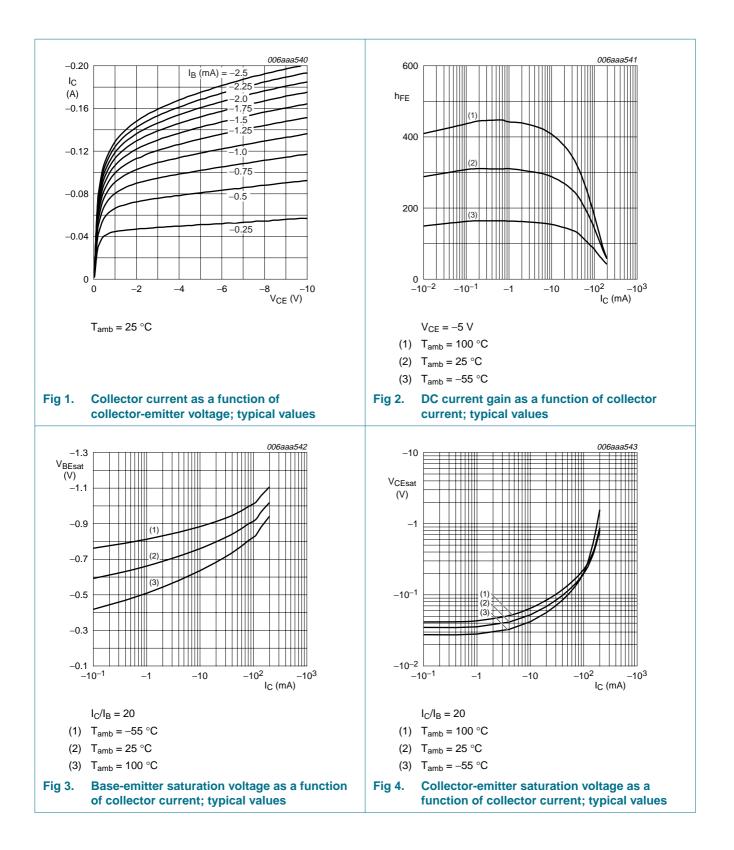
[1] V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.

[2] V_{BE} decreases by about 2 mV/K with increasing temperature.

[3] The smaller of the two values is taken as the numerator.

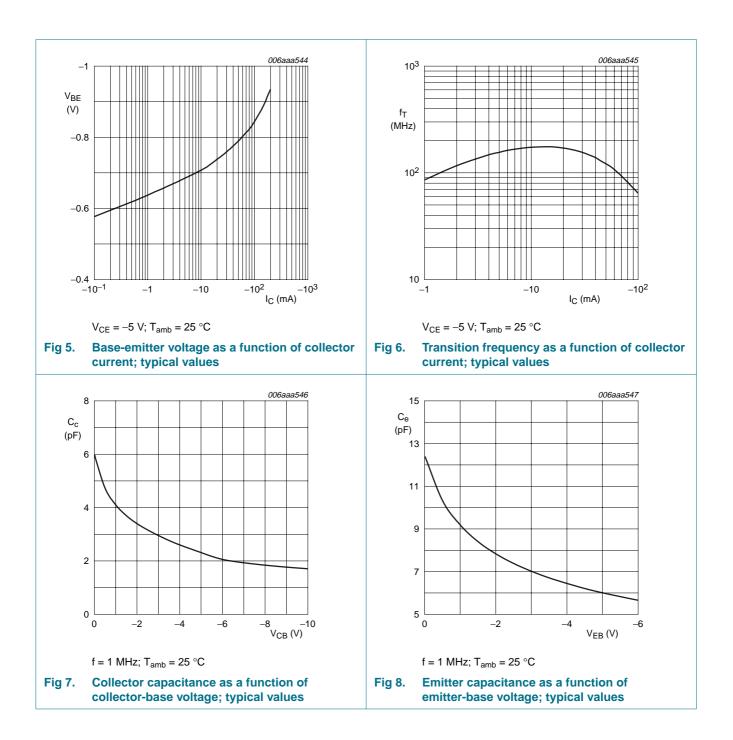
[4] The smaller of the two values is subtracted from the larger value.

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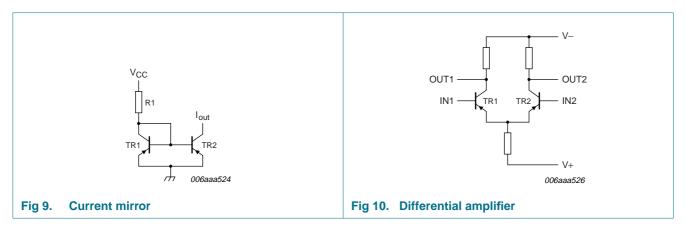
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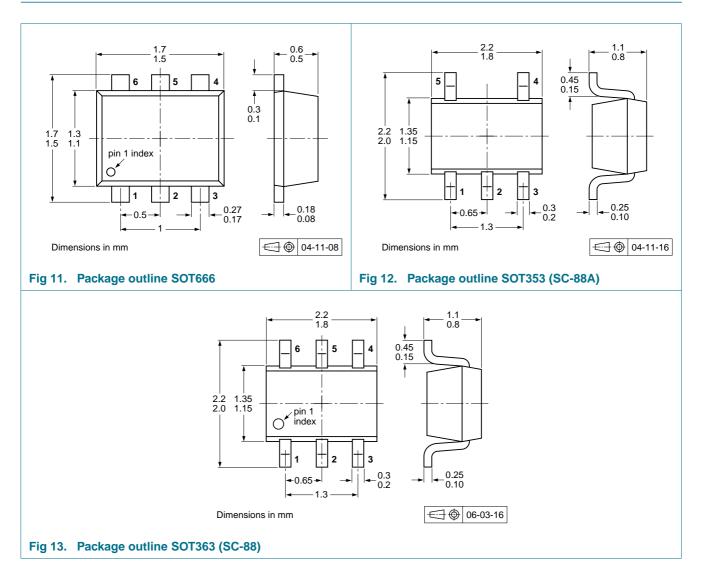


PNP/PNP matched double transistors

8. Application information



9. Package outline



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10. Packing information

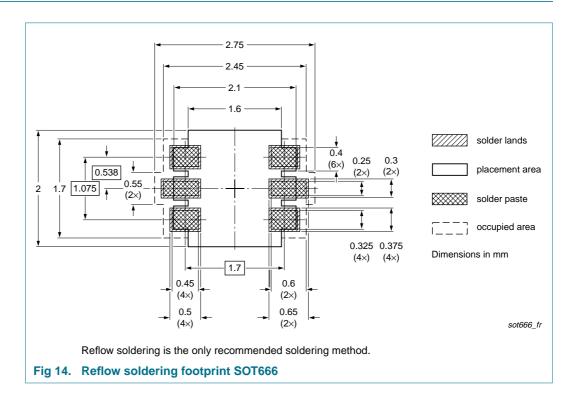
Table 9. **Packing methods** The indicated -xxx are the last three digits of the 12NC ordering code.[1] Type number Package Description **Packing quantity** 3000 4000 8000 10000 PMP5501V SOT666 2 mm pitch, 8 mm tape and reel -315 ---4 mm pitch, 8 mm tape and reel _ -115 --PMP5501G SOT353 4 mm pitch, 8 mm tape and reel -115 ---135 4 mm pitch, 8 mm tape and reel; T1 PMP5501Y SOT363 2 -115 -135 --**3** -125 4 mm pitch, 8 mm tape and reel; T2 ---165

[1] For further information and the availability of packing methods, see Section 14.

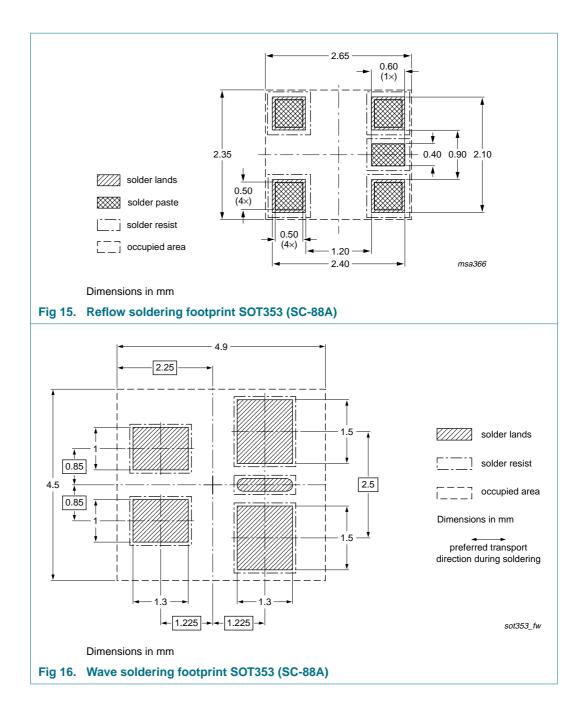
[2] T1: normal taping

[3] T2: reverse taping

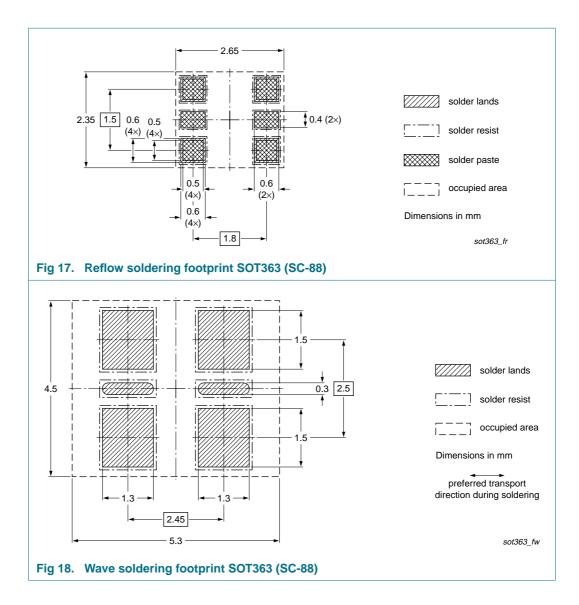
11. Soldering



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12. Revision history

Release date	Data sheet status	Change notice	Supersedes		
20090828	Product data sheet	-	PMP5501V_G_Y_2		
	0				
 Figure 14 "F 	Reflow soldering footprint S	OT666": updated			
 Figure 16 "Wave soldering footprint SOT353 (SC-88A)": updated 					
 Figure 17 "Reflow soldering footprint SOT363 (SC-88)": updated 					
Figure 18 "V	Vave soldering footprint SC	0T363 (SC-88)": updated	1		
20060919	Product data sheet	-	PMP5501G_Y_1		
	20090828 This data sh including ne content. Figure 14 "F Figure 16 "V Figure 17 "F Figure 18 "V	20090828 Product data sheet • This data sheet was changed to reflect including new legal definitions and disc content. • Figure 14 "Reflow soldering footprint S • Figure 16 "Wave soldering footprint SC • Figure 17 "Reflow soldering footprint SC • Figure 18 "Wave soldering footprint SC	20090828 Product data sheet - • This data sheet was changed to reflect the new company name including new legal definitions and disclaimers. No changes we content. • • Figure 14 "Reflow soldering footprint SOT666": updated • • Figure 16 "Wave soldering footprint SOT353 (SC-88A)": updated • • Figure 17 "Reflow soldering footprint SOT363 (SC-88)": updated • • Figure 18 "Wave soldering footprint SOT363 (SC-88)": updated •		

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13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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PMP5501V_G_Y_3 Product data sheet

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